
Investigation of Wavelength Dependence of Conversion Efficiency using Xenon Jet for LPP EUV Light Source

EUVA

(**Ext**reme **U**ltraviolet Lithography System Development **A**ssociation)
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**3rd International EUVL Symposium
1- 4 November, 2004
Miyazaki, Japan**

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Introduction

- High power EUV light sources require high conversion efficiencies (CE) in order to reduce the necessary input power.
- Currently a conversion efficiency of 1.0% (2% BW, 2π sr) using a frozen xenon target and a Nd:YAG laser oscillating at 1064nm is obtained.
- Target:
 - 1) To obtain guidelines for higher CE development.
 - 2) Investigation of an optimum laser wavelength for CE.
- This poster outlines the dependence of the conversion efficiency on various parameters, e.g. laser energy, at different wavelengths (266nm, 532nm and 1064nm) for a Xenon jet target.

Experimental Setup

■ Laser

Wavelength : 1064nm(~450mJ), 532nm(~165mJ)
266nm(~55mJ)

Pulse width : ~8ns (fwhm)

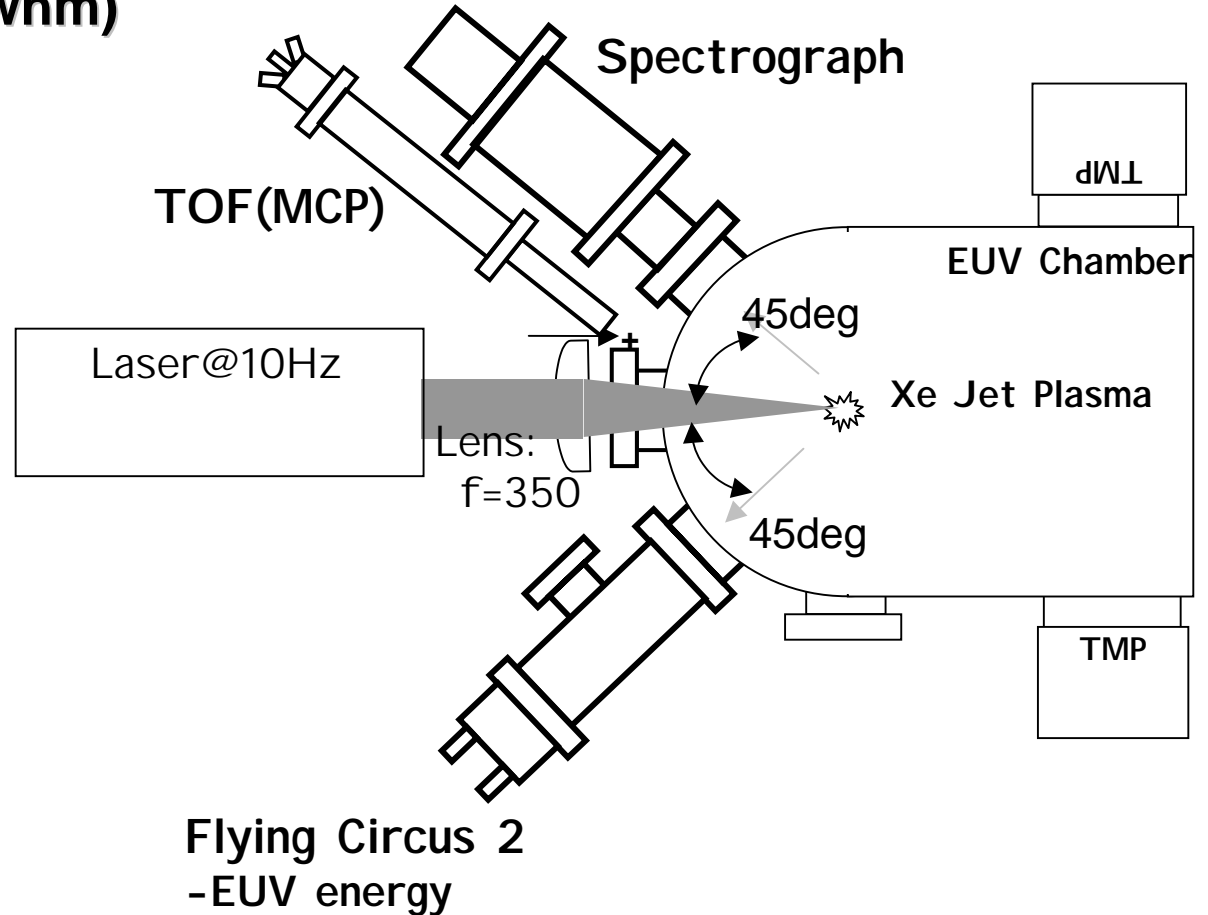
Rep. rate : 10Hz

■ Target

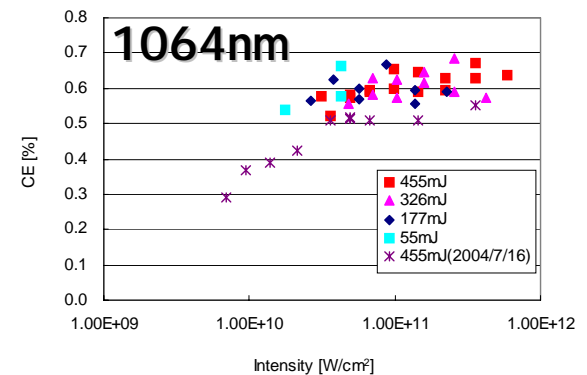
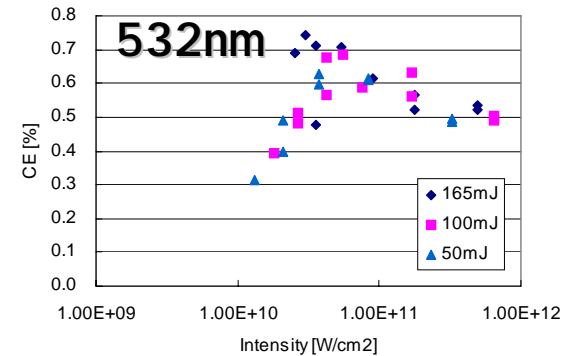
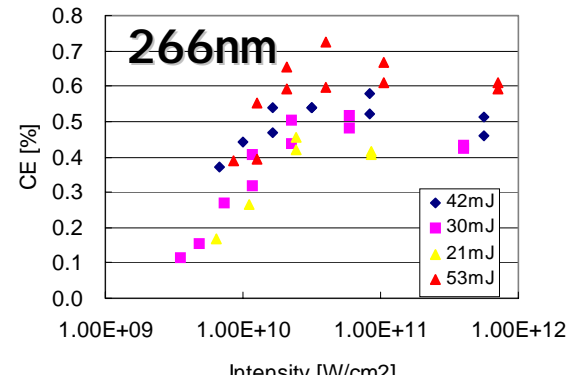
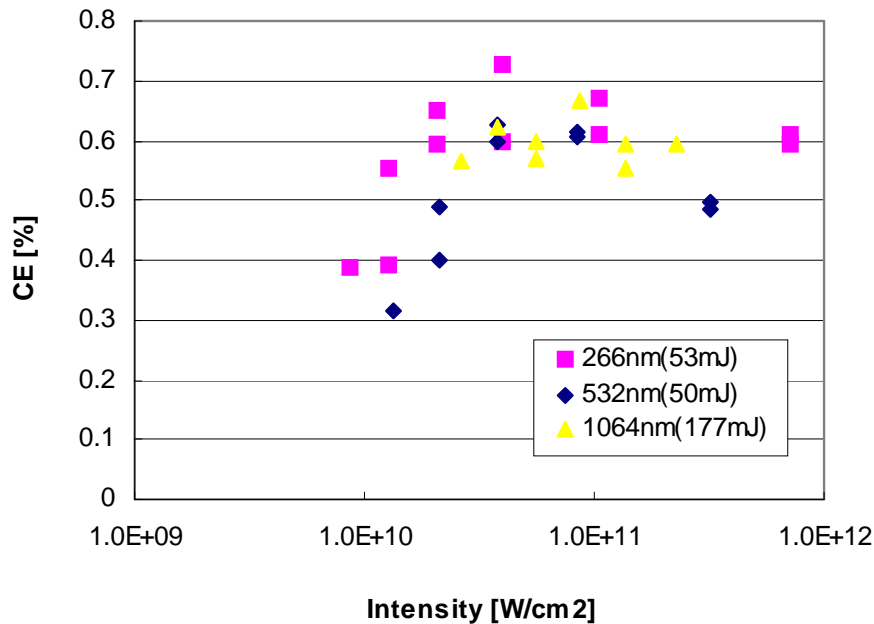
Xenon jet
(350 μ m max)

■ Evaluations

- ✓ EUV energy (CE)
- ✓ Spectrum
- ✓ Fast ion



Experimental Results (CE vs. Intensity)



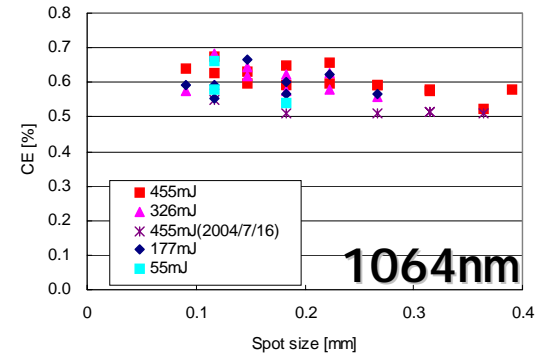
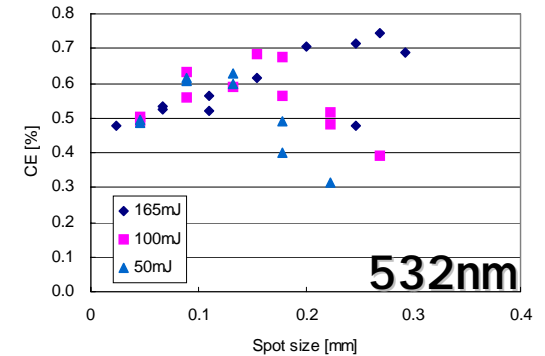
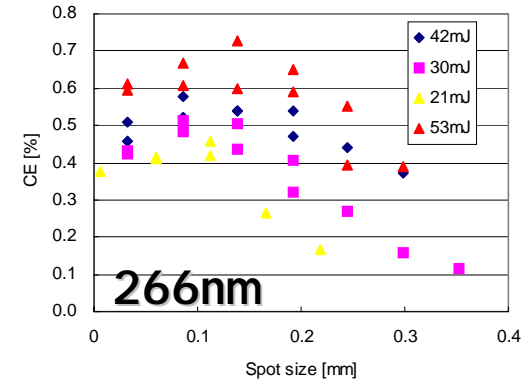
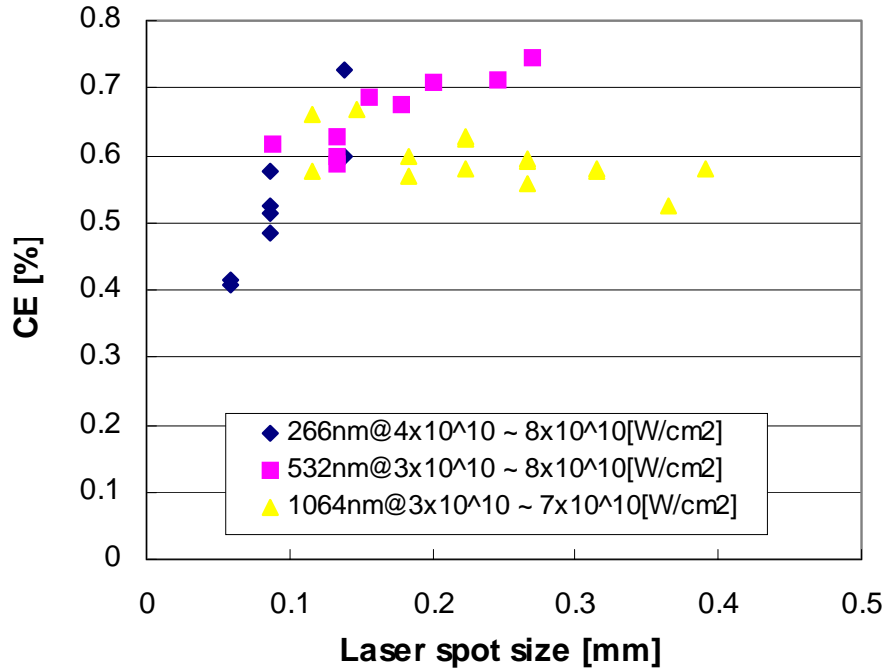
✓ Optimum Laser Intensity for CE at different wavelengths:

266nm: $5 \times 10^{10} \text{ W/cm}^2$

532nm: $5 \times 10^{10} \text{ W/cm}^2$

1064nm: $\sim 1 \times 10^{11} \text{ W/cm}^2$

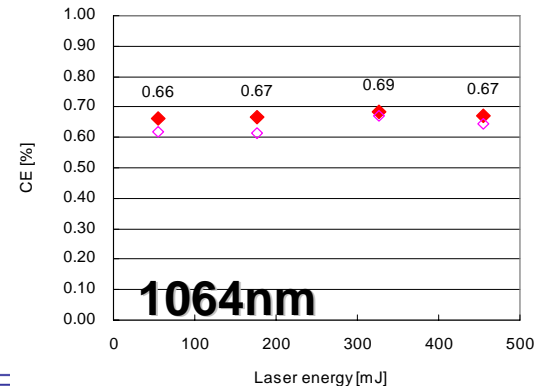
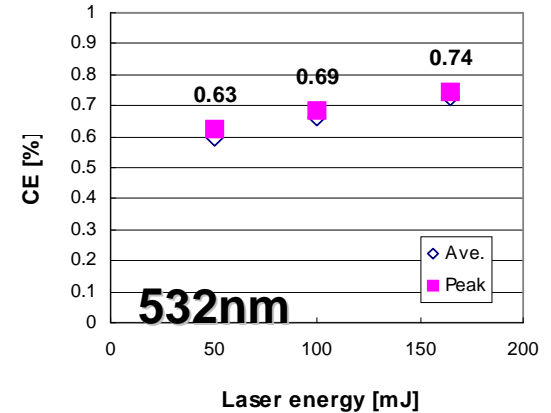
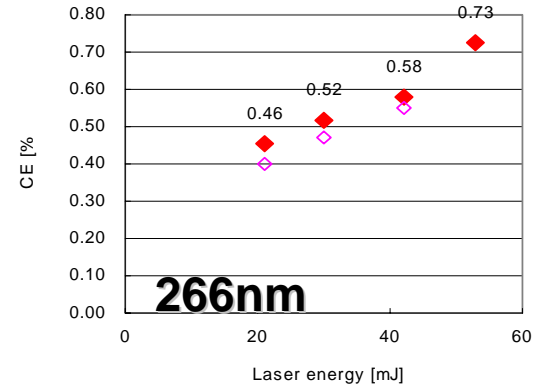
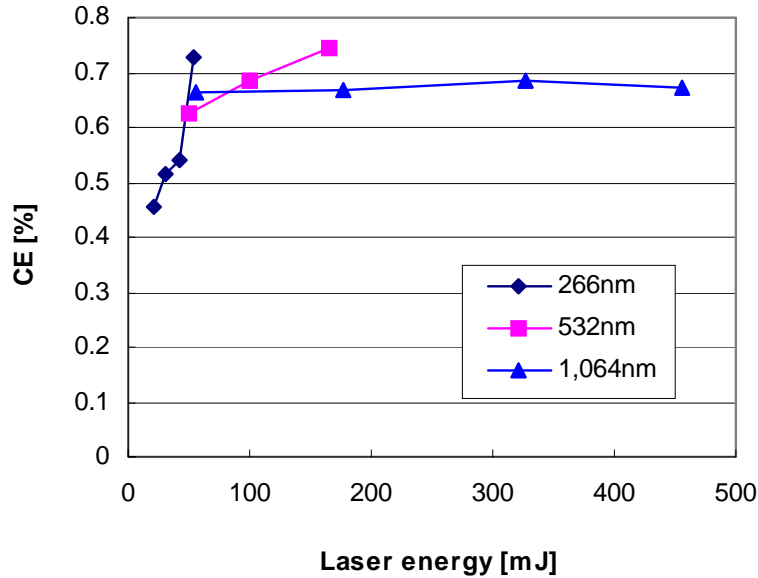
Experimental Results (CE vs. Spot size)



✓ Best Laser Spot size for CE at different wavelengths:

266nm: 0.14 mm
 532nm: 0.28 mm
 1064nm: 0.15 mm

Experimental Results (CE vs. Laser energy)



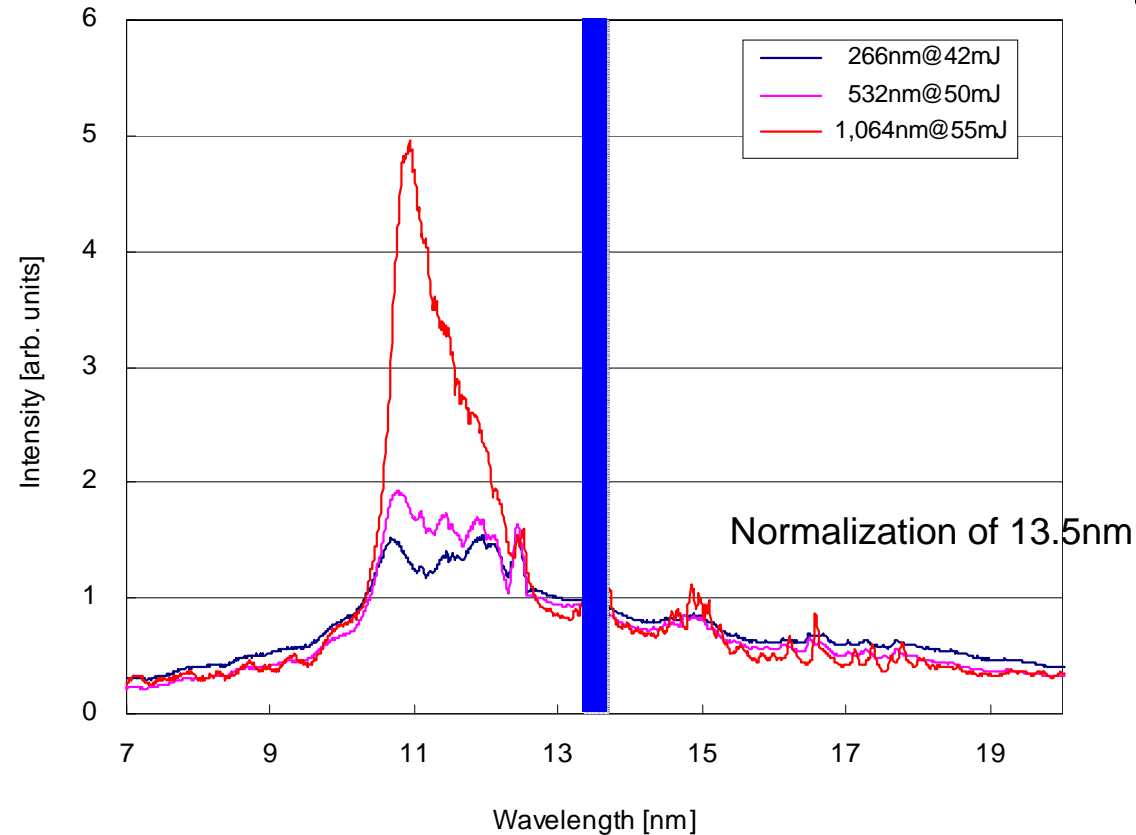
Maximum CE at different wavelengths:

266nm : 0.73% @ 55mJ
 532nm : 0.74% @ 165mJ
 1064nm : 0.69% @ 460mJ

Experimental Results (Spectra)

Spectrograph (Shinseiki)

- Grazing Incidence Spectrograph
- Grating : 1200 l/mm
- Slit : 25 μm
- Back illuminated CCD



✓ Lower plasma emission at 11nm for 266nm wavelength laser compared to 1064nm laser.

Experimental Setup (TOF)

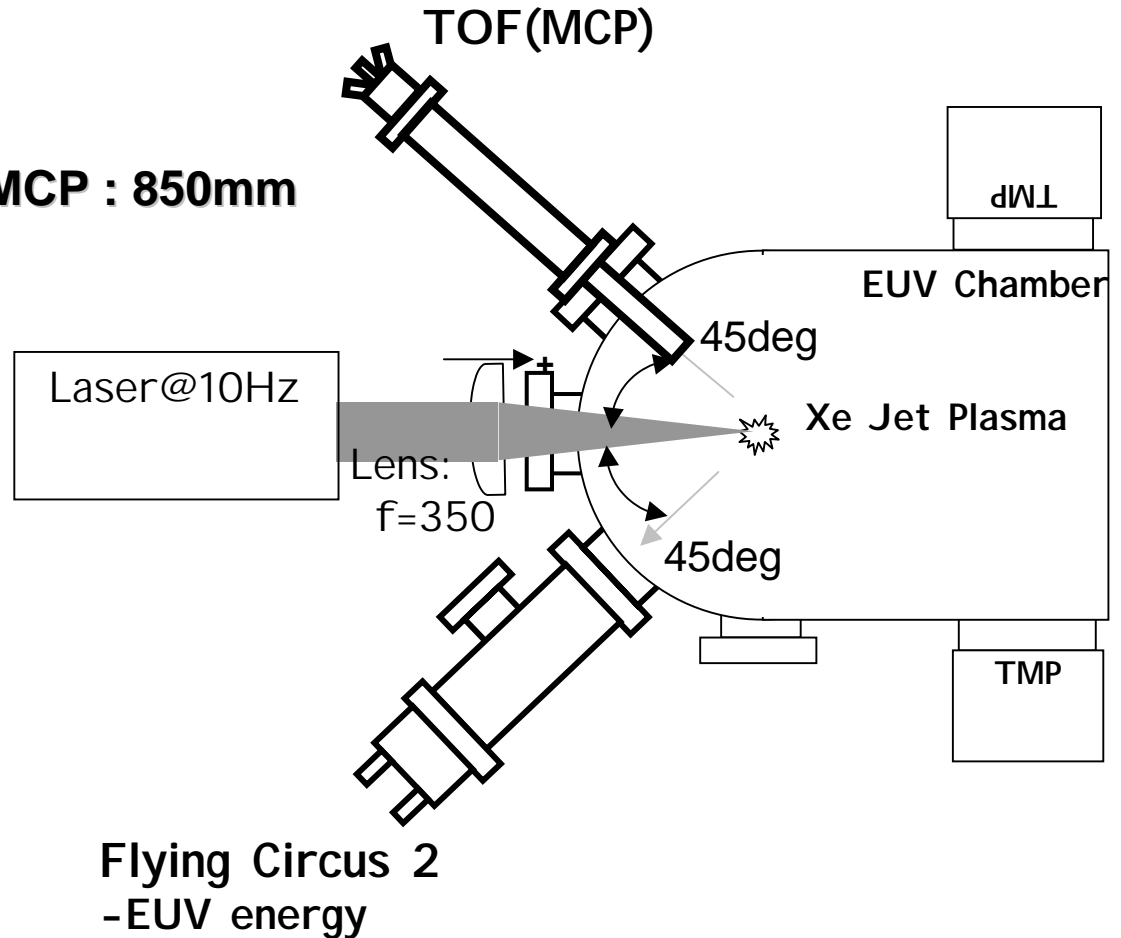
■ MCP

Maker : Hamamatsu Photonics K.K.

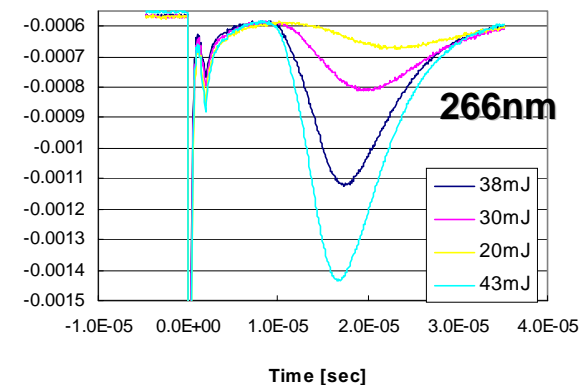
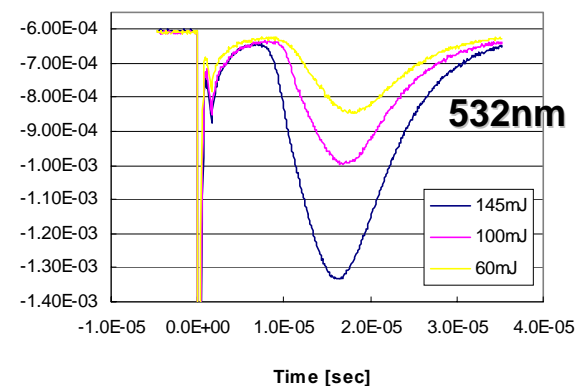
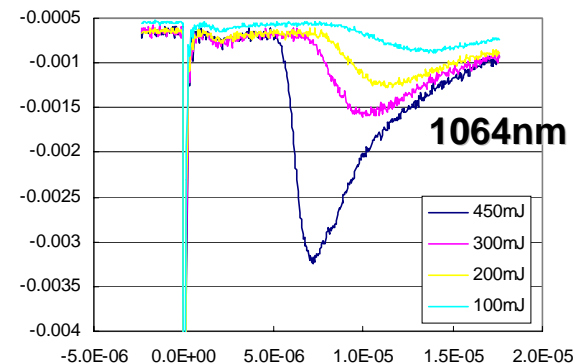
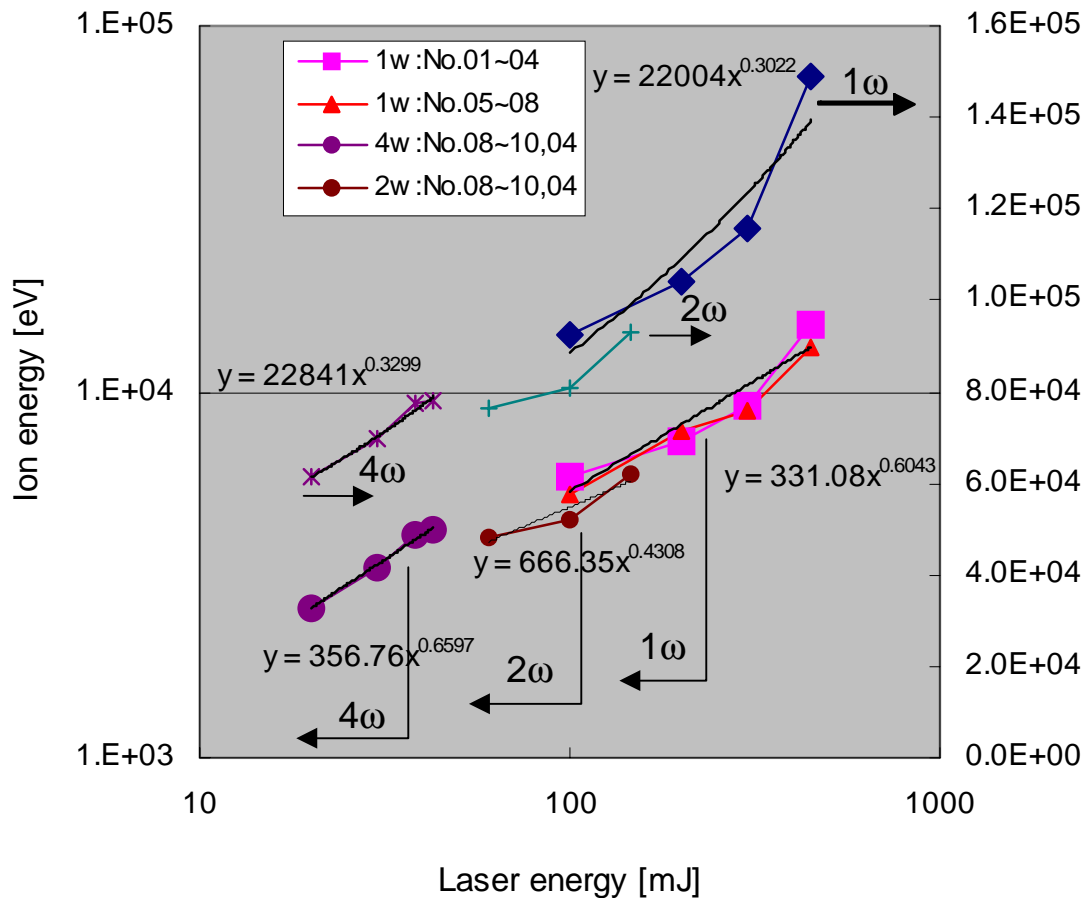
Type: F4655-13

Bias voltage: 1.4kV

■ Distance from Plasma to MCP : 850mm

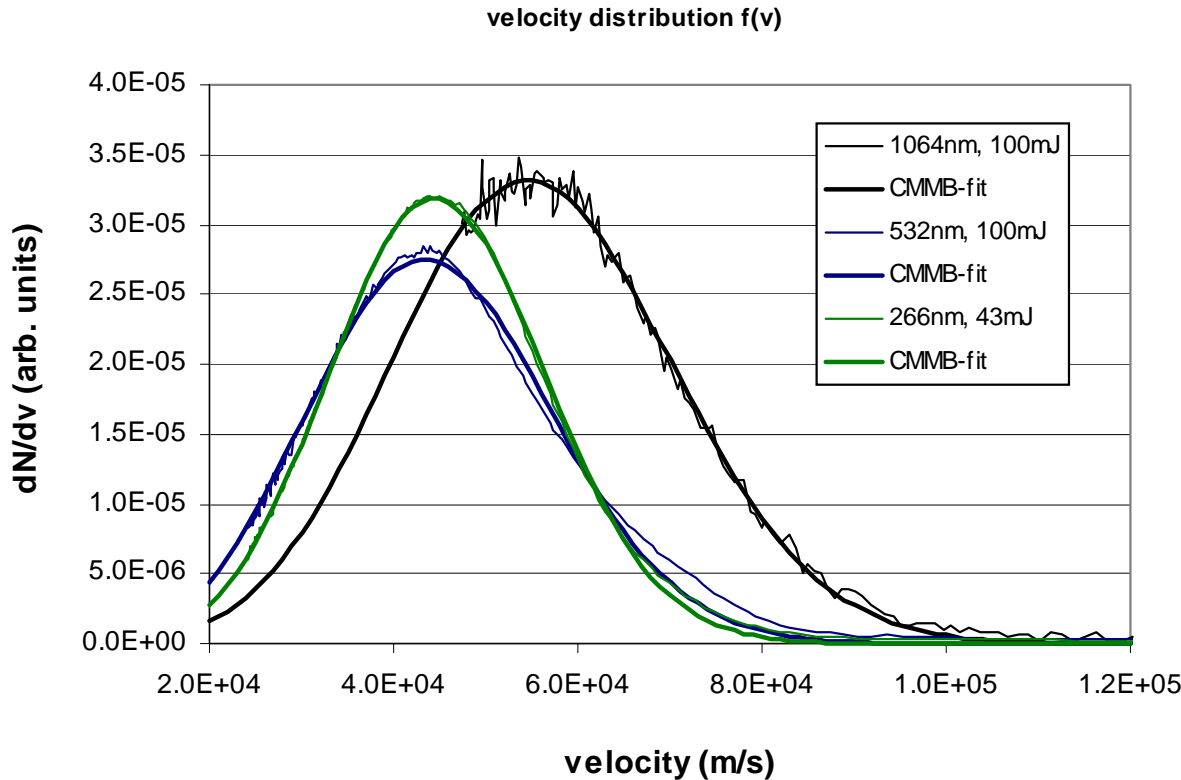


Experimental Results (Fast ion energy)



✓ Fast ion energy depends on laser energy and not the laser wavelength.

Experimental Results (Ion velocity distribution)



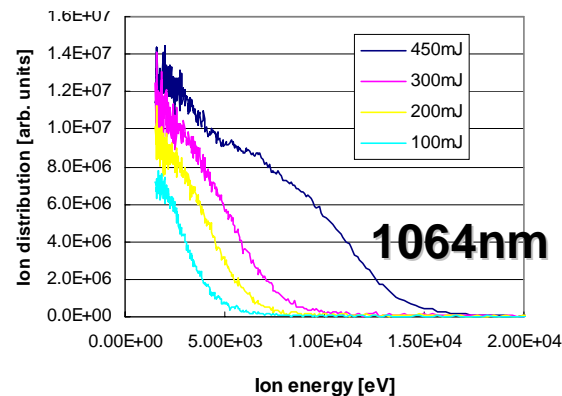
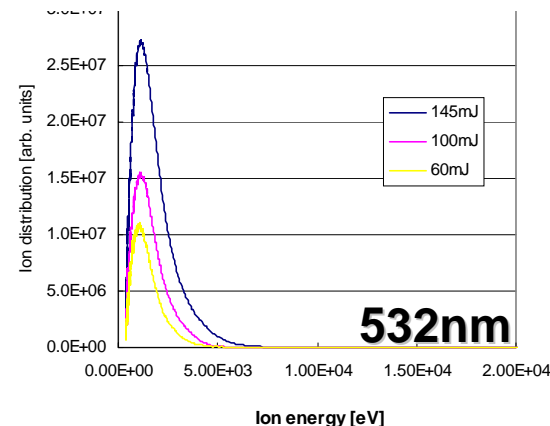
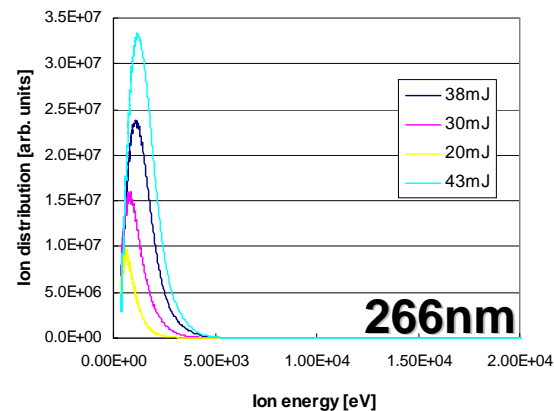
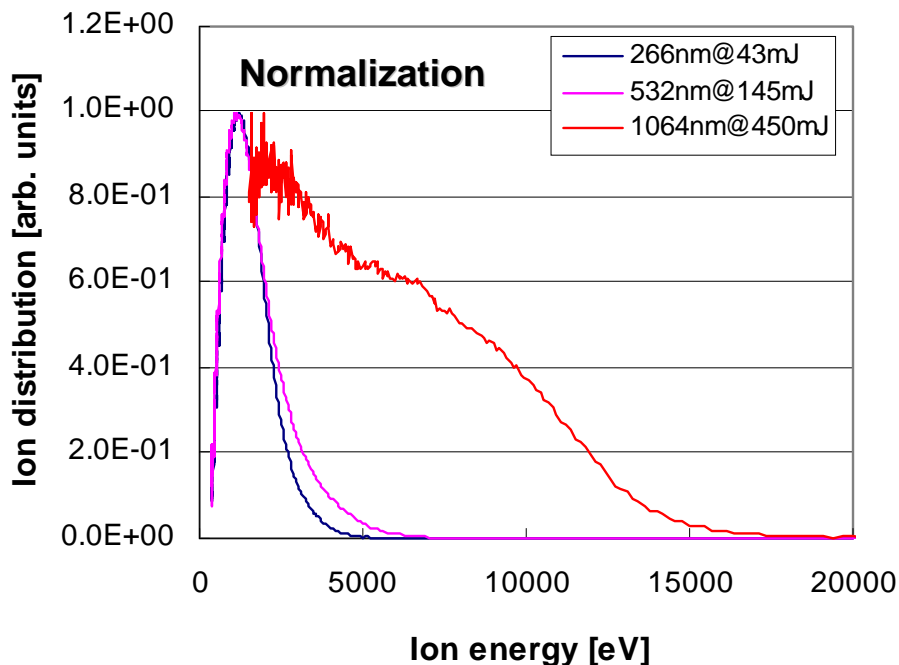
Fitting parameter

	T (eV)	v_{CM} (m/s)	v_{max} (m/s)
266nm	239	32583	45013
532nm	335	26438	43947
1064nm	416	37769	53525

$$f(v) \sim v^3 \text{Exp}[-1/2 m (v-v_{CM})^2 / (k_b T)]$$

✓ Plasma close to thermal equilibrium – most ion distributions well described by a shifted center-of-mass Maxwell-Boltzmann distribution.

Experimental Results (Ion energy distribution)



✓ The ion distribution shows two peaks for 450mJ at 1064nm.

Summary

- ✓ **Maximum CE obtained is approximately 0.7%.**
- ✓ **At 266nm the CE shows strong dependence of laser energy.**
- ✓ **Max. CE limited by available laser energy for 266nm and 532nm.**
- ✓ **Reduced plasma emission at 11nm for 266nm laser wavelength compared to 1064nm.**
- ✓ **Fast ion energy depends on laser energy not laser wavelength.**

Acknowledgements

This work was performed under the management of the
Extreme Ultraviolet Lithography System Development Association



a research and development program of

NEDO.